

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2 S C 5 3 8 6

HORIZONTAL DEFLECTION OUTPUT FOR HIGH RESOLUTION DISPLAY, COLOR TV

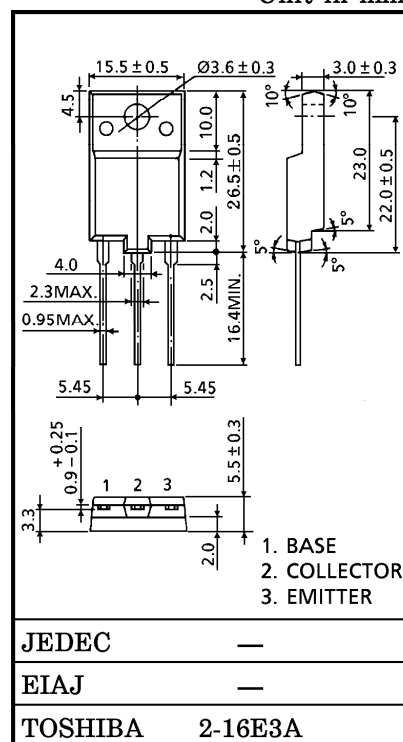
HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CBO} = 1500 \text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3 \text{ V (Max.)}$
- High Speed : $t_f = 0.15 \mu\text{s (Typ.)}$
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS (T_a = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB0}	1500	V
Collector-Emitter Voltage		V_{CEO}	600	V
Emitter-Base Voltage		V_{EB0}	5	V
Collector Current	DC	I_C	8	A
	Pulse	I_{CP}	16	
Base Current		I_B	4	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)		P_C	50	W
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55\sim 150$	$^\circ\text{C}$

Unit in mm



Weight : 5.5 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1500\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	10	μA
Emitter-Base Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	600	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	15	—	35	
		$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 6\text{ A}$	4.3	—	7.5	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 6\text{ A}, I_B = 1.5\text{ A}$	—	—	3	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 6\text{ A}, I_B = 1.5\text{ A}$	—	1.0	1.5	V
Transition Frequency		f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	1.7	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	105	—	pF
Switching Time	Storage Time	t_{stg}	$I_{CP} = 5\text{ A}, I_{B1}(\text{end}) = 1.0\text{ A}$ $f_H = 64\text{ kHz}$	—	2.5	3.5	μs
	Fall Time	t_f		—	0.15	0.3	

